

INFORMATION DISCLOSURE CITATION
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ATTY DOCKET NO.
BUR920010146US2

SERIAL NO. 10/660,048
Not Yet Assigned

Lanzerotti et al.

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GROUP
2826 Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<u>TD</u>	4,885,614	12/05/1989	Furukawa et al.			
	5,116,455	05/26/1992	Daly			
	5,321,302	06/14/1994	Shimawaki			
	5,338,945	08/16/1994	Baliga et al.			
	5,360,986	11/01/1994	Candelaria			
	5,404,028	04/04/1995	Metzger et al.			
	5,468,658	11/21/1995	Bayraktaroglu			
	5,557,118	09/17/1996	Hashimoto			
	5,731,626	03/24/1998	Eaglesham et al.			
	5,783,845	07/21/1998	Kondo et al.			
<u>TD</u>	5,986,287	11/16/1999	Eberl et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<u>TD</u>	JP11312685A	11/09/1999	Japan w/Abstract				✓
	JP2000012558A	01/14/2000	Japan w/Abstract				✓
	JP92000174033A	06/23/2000	Japan w/Abstract				✓
<u>TD</u>	WO 98/26457	06/18/1998	Germany				✓

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>TD</u>	Lanzerotti et al., "Suppression of Boron Outdiffusion in SiGe HBTs by Carbon Incorporation", 1996 IEEE, pp. 10.2.1 - 10.2.4
<u>TD</u>	Stock et al. "Carbon Incorporation in Silicon for Suppressing Interstitial-Enhanced Boron Diffusion", Applied Physics Letter, March 13, 1995, Vol. 66, Issue 11, pp. 1370-1372

EXAMINER

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TE	6,043,139	03/28/2000	Eaglesham et al.			
	6,096,617	08/01/2000	Kizuki			
	6,107,151	08/22/2000	Enquist			
	6,229,197	05/08/2001	Plumton et al.			
	6,534,371	03/2003	Coolbaugh et al.			
	6,509,242	01/2003	Frei et al.			
	5,814,843	09/1998	Ohkubo, Michio			
TE	5,387,807	02/1995	Bayraktaroglu, Burhan			

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						YES	NO

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TE	Ghanti et al., "Control of Implant-Damage-Enhanced Boron Diffusion in Epitaxially Grown Si/p-Si _{1-x} Ge _x /n-Si Heterojunction Bipolar Transistors", Journal of Electronic Materials, Vol. 24, No. 8, 1995, pp. 999-1002
TE	Bodnar et al., "Growth of Ternary Alloy Si _{1-x} Ge _x Cy By Rapid Thermal Chemical Vapor Deposition", Journal Vac. Science Technology, A., Vol. 1. 13, N. 5, Sept/Oct. 1995, pp.2336-2340

EXAMINER *H. D. D.*

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TZ		Poate et al., "Ion Implantation and Transient Enhanced Diffusion", IEDM 95-77, IEEE 1995, pp. 4.1.1 - 4.1.4

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